(d) REMARKS

The claims are 17-22 with claim 17 the sole independent claim. Claim 17 has been amended to clarify the intended invention and reconsideration of the claims is expressly requested.

Claims 17 and 22 was rejected as anticipated by Nakatani '917. Claims 18-20 were rejected as obvious over Nakatani '917 in view of Igarashi '571. Claim 21 was rejected as obvious over Nakatani and Igarashi in view of Kieser '641. The grounds of rejection are respectfully traversed.

Initially, claim 17 has been amended to provide that a gas gate prevents diffusion of p-type dopant in the second chamber into the first chamber. Support is found on page 19, lines 16-19; page 35, lines 3-6; page 63, lines 5-10 and page 83, lines 15-18.

In the present claimed invention, a separating path between the first and second chambers, i.e., between the i-type and p-type layer forming chambers is a gas gate. However, in Nakatani, buffer chamber 13, provided between reaction chambers 1 and 2, is not a gas gate because Nakatani discloses that the buffer chamber, as a narrow path, cannot prevent diffusion of a p-type dopant from the p-type layer- forming reaction chamber into the i-type layer- forming reaction chamber. Therefore, Nakatani has no concept of employing a gate gas in the buffer chamber.

Nakatani discloses that separators 11 have gaps 14 therebetween. The gaps 14 were formed to allow the passage of a reaction gas. Nakatani also teaches that in the system of Fig. 1, slight amounts of gas usually penetrate the second reaction chamber through buffer chamber 13 and that this is unavoidable. Nakatani further teaches regarding

Fig. 4 that even with separators gas-containing boron from the p-type reactor is accumulated in the i-type layer.

Furthermore, because the separator 11of Nakatani is separated from a high frequency applying electrode, the separator of Nakatani is different from the fin-shaped electrode.

Finally, it is clear from the drawings that a portion of Nakatani for supplying a raw material gas into the chamber is not shielded. Therefore, such portion of Nakatani is different from the portion of the present invention (claim 22) for supplying a raw material gas into the chamber and having a member for shielding the substrate from the flow of the raw material gas.

Wherefore, it is requested that the claims be allowed and that the case be passed to issue.

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